Jordan D Greenlee

List of Publications by Citations

33 papers	665 citations	16 h-index	25 g-index
34 ext. papers	740 ext. citations	2.4 avg, IF	3.49 L-index

#	Paper	IF	Citations
33	Structural, Optical, and Electrical Characterization of Monoclinic Ga2O3 Grown by MOVPE on Sapphire Substrates. *Journal of Electronic Materials*, **2016**, 45, 2031-2037	1.9	92
32	Substrate-Dependent Effects on the Response of AlGaN/GaN HEMTs to 2-MeV Proton Irradiation. *IEEE Electron Device Letters*, **2014**, 35, 826-828	4.4	65
31	Observation and control of the surface kinetics of InGaN for the elimination of phase separation. *Journal of Applied Physics*, **2012**, 112, 014909	2.5	34
30	Symmetric Multicycle Rapid Thermal Annealing: Enhanced Activation of Implanted Dopants in GaN. *ECS Journal of Solid State Science and Technology*, **2015**, 4, P382-P386	2	32
29	Selective p-type Doping of GaN:Si by Mg Ion Implantation and Multicycle Rapid Thermal Annealing. *ECS Journal of Solid State Science and Technology*, **2016**, 5, P124-P127	2	32
28	Multicycle rapid thermal annealing optimization of Mg-implanted GaN: Evolution of surface, optical, and structural properties. *Journal of Applied Physics*, **2014**, 116, 063502	2.5	28
27	Characterization of an Mg-implanted GaN p diode. *Physica Status Solidi (A) Applications and Materials Science*, **2015**, 212, 2772-2775	1.6	28
26	In-situ oxygen x-ray absorption spectroscopy investigation of the resistance modulation mechanism in LiNbO2 memristors. *Applied Physics Letters*, **2012**, 100, 182106	3.4	27
25	Degradation mechanisms of 2 MeV proton irradiated AlGaN/GaN HEMTs. *Applied Physics Letters*, **2015**, 107, 083504	3.4	26
24	Improved Vertical GaN Schottky Diodes with Ion Implanted Junction Termination Extension. *ECS Journal of Solid State Science and Technology*, **2016**, 5, Q176-Q178	2	26
23	Proton Radiation-Induced Void Formation in Ni/Au-Gated AlGaN/GaN HEMTs. *IEEE Electron Device Letters*, **2014**, 35, 1194-1196	4.4	23
22	Improvements in the Annealing of Mg Ion Implanted GaN and Related Devices. *IEEE Transactions on Semiconductor Manufacturing*, **2016**, 29, 343-348	2.6	23
21	Impact of Surface Passivation on the Dynamic ON-Resistance of Proton-Irradiated AlGaN/GaN HEMTs. *IEEE Electron Device Letters*, **2016**, 37, 545-548	4.4	23
20	Ultraviolet detector based on graphene/SiC heterojunction. *Applied Physics Express*, **2015**, 8, 041301	2.4	21
19	Comparison of Interfacial and Bulk Ionic Motion in Analog Memristors. *IEEE Transactions on Electron Devices*, **2013**, 60, 427-432	2.9	21
18	Halide based MBE of crystalline metals and oxides. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 155-160		18
17	In situ investigation of the channel conductance of a Li1CoO2 (0 . *Applied Physics Letters*, **2013**, 102, 213502	3.4	16

List of Publications

16	Characterization of a selective AlN wet etchant. *Applied Physics Express*, **2015**, 8, 036501	2.4	15
15	Spatial Mapping of Pristine and Irradiated AlGaN/GaN HEMTs With UV Single-Photon Absorption Single-Event Transient Technique. *IEEE Transactions on Nuclear Science*, **2016**, 63, 1995-2001	1.7	14
14	Radiation Effects on LiNbO $_2$ Memristors for Neuromorphic Computing Applications. *IEEE Transactions on Nuclear Science*, **2013**, 60, 4555-4562	1.7	12
13	Defect reduction in MBE-grown AlN by multicycle rapid thermal annealing. *Electronic Materials Letters*, **2016**, 12, 133-138	2.9	11
12	Liquid Phase Electro-Epitaxy of Memristive LiNbO2 Crystals. *Crystal Growth and Design*, **2014**, 14, 2218-2222	3.5	11
11	Comparison of AlN Encapsulants for Bulk GaN Multicycle Rapid Thermal Annealing. *ECS Journal of Solid State Science and Technology*, **2015**, 4, P403-P407	2	10
10	Comparison of AlN encapsulants for high-temperature GaN annealing. *Applied Physics Express*, **2014** , 7, 121003	2.4	10
9	Hyperspectral Electroluminescence Characterization of OFF-State Device Characteristics in Proton Irradiated High Voltage AlGaN/GaN HEMTs. *ECS Journal of Solid State Science and Technology*, **2016**, 5, Q289-Q293	2	10
8	Thermal etching of nanocrystalline diamond films. *Diamond and Related Materials*, **2015**, 59, 116-121	3.5	8
7	Spatiotemporal drift-diffusion simulations of analog ionic memristors. *Journal of Applied Physics*, **2013**, 114, 034504	2.5	7
6	Molecular beam epitaxy growth of niobium oxides by solid/liquid state oxygen source and lithium assisted metal-halide chemistry. *Journal of Crystal Growth*, **2015**, 425, 225-229	1.6	6
5	Temporary Bonding with Polydimethylglutarimide Based Lift Off Resist as a Layer Transfer Platform. *ECS Journal of Solid State Science and Technology*, **2015**, 4, P190-P194	2	6
4	Degradation mechanisms of AlGaN/GaN HEMTs on sapphire, Si, and SiC substrates under proton irradiation **2014**,		6
3	In situ Auger probe enabling epitaxy composition control of alloys by elemental surface analysis. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2013**, 31, 03C126	1.3	2
2	Elimination of Basal Plane Dislocations in Epitaxial 4H-SiC via Multicycle Rapid Thermal Annealing. *Materials Science Forum*, **2015**, 821-823, 297-302	0.4	1
1	UV Single-Photon Absorption Single-Event Transient Testing of Pristine and Irradiated AlGaN/GaN HEMTs **2015**,		1